

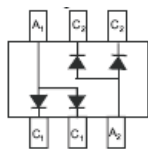
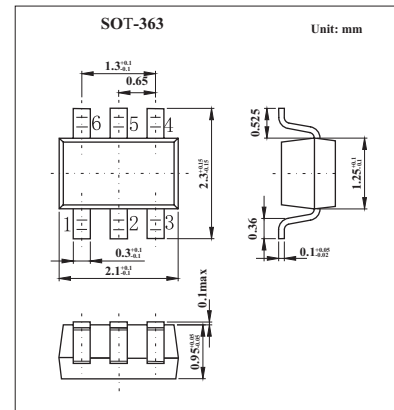
Surface Mount Schottky Barrier Diode Arrays

KAT54TW,ADW,CDW,SDW,BRW

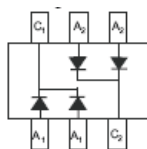
(BAT54TW,ADW,CDW,SDW,BRW)

■ Features

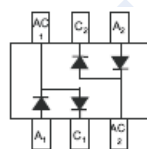
- Low Forward Voltage Drop
- Fast Switching
- Ultra-Small Surface Mount Package
- PN Junction Guard Ring for Transient and ESD Protection



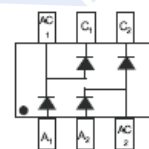
KAT54ADW



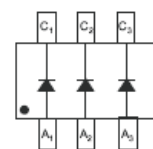
KAT54CDW



KAT54SDW



KAT54BRW



KAT54TW

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	VRRM	30	V
Working Peak Reverse Voltage	VRWM		
DC Blocking Voltage	VR		
Forward Continuous Current *	IF	200	mA
Repetitive Peak Forward Current *	IFRM	300	mA
Forward Surge Current * @ $t < 1.0\text{s}$	IFSM	600	mA
Power Dissipation*	Pd	200	mW
Thermal Resistance, Junction to Ambient Air*	R θ JA	625	$^\circ\text{C}/\text{W}$
Operating and Storage Temperature Range	Tj, TSTG	-65 to +125	$^\circ\text{C}$

*. Device mounted on FR-4 PCB, 1 inch X 0.85 inch X 0.062 inch;

KAT54TW,ADW,CDW,SDW,BRW (BAT54TW,ADW,CDW,SDW,BRW)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Reverse Breakdown Voltage *	$V_{(BR)}$	$I_R = 100 \mu A$	30			V
Maximum Forward Voltage *	V_{FM}	$I_F = 0.1mA$ $I_F = 1mA$ $I_F = 10mA$ $I_F = 30mA$ $I_F = 100mA$			240 320 400 500 1000	mV
Peak Reverse Current 8	I_R	$V_R = 25V$			2.0	μA
Junction Capacitance	C_j	$V_R = 1.0V, f = 1.0MHz$			10	pF
Reverse Recovery Time	t_{rr}	$I_F = 10mA$ through $I_R = 10mA$ to $I_R = 1.0mA, R_L = 100 \Omega$			5	ns

* Short duration test pulse used to minimize self-heating effect.

■ Marking

NO.	KAT54ADW	KAT54CDW	KAT54SDW	KAT54BRW	KAT54TW
Marking	KL6	KL7	KL8	KLB	KLA